

forming an EL layer over the pixel electrode;
forming a second electrode over the EL layer,
wherein the EL layer is selectively formed through an ink jet method,
wherein the insulating film comprises silicon,
wherein the insulating film is capable of preventing penetration of alkaline metal.

2. (Amended) A method for manufacturing an electrical device, said method comprising the steps of:

forming at least a thin film transistor;
forming an insulating film over the thin film transistor;
forming a pixel electrode over the insulating film, said pixel electrode being connected to the thin film transistor;
forming an EL layer over the pixel electrode;
forming a second electrode over the EL layer,
wherein the EL layer is selectively formed through an ink jet method
wherein the insulating film comprises aluminum oxide,
wherein the insulating film is capable of preventing penetration of alkaline metal.

3. (Amended) A method for manufacturing an electrical device, said method comprising the steps of:

forming at least a thin film transistor on an insulating surface;
forming an insulating film over the thin film transistor;
forming a pixel electrode over the insulating film, said pixel electrode being connected to the thin film transistor;
forming an EL layer over the pixel electrode;
forming a second electrode over the EL layer;

wherein the EL layer is selectively formed through an ink jet method,
wherein the insulating film comprises diamond like carbon,
wherein the insulating film is capable of preventing penetration of alkaline
metal.

4. (Amended) A method for manufacturing an electrical device, said method comprising the steps of:

forming at least a thin film transistor on an insulating surface;

forming an insulating film over the thin film transistor;

forming a pixel electrode over the insulating film, said pixel electrode being
connected to the thin film transistor;

forming an EL layer over the pixel electrode;

forming a second electrode over the EL layer,

wherein the EL layer is selectively formed through an ink jet method in an
atmosphere comprising nitrogen,

wherein the insulating film is capable of preventing penetration of alkaline
metal.

5. (Amended) A method for manufacturing an electrical device comprising the
steps of:

forming at least a thin film transistor on an insulating surface;

forming an insulating film over the thin film transistor;

forming a pixel electrode over the insulating film, said pixel electrode being
connected to the thin film transistor;

forming an EL layer over the pixel electrode;

forming a second electrode over the EL layer,

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wherein the EL layer is selectively formed through an ink jet method in an atmosphere comprising argon,
wherein the insulating film is capable of preventing penetration of alkaline metal.

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7. (Amended) A method according to claim 1, wherein an organic resin film is formed, the thin film transistor and the insulating film.

C8
10. (Amended) A method according to claim 4, wherein an organic resin film is formed between the thin film transistor and the insulating film.

C9
21. (Amended) A method according to claim 5, wherein an organic resin is formed between the thin film transistor and the insulating film.

C10
4 30. (Amended) A method according to claim 1, wherein one of the pixel electrode and the second electrode comprises at least one selected from the group consisting of magnesium (Mg), lithium (Li), cesium (Cs), barium (Ba), potassium (K), beryllium (Be), and calcium (Ca).

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31. (Amended) A method according to claim 1, wherein the insulating film comprises at least one selected from the group consisting of silicon nitride oxide and silicon nitride.

32. (Amended) A method according to claim 2, wherein an organic resin is formed between the thin film transistor and the insulating film.

¹¹
~~33.~~ (Amended) A method according to claim ⁸~~7~~, wherein one of the pixel electrode and the second electrode comprises at least one selected from the group consisting of magnesium (Mg), lithium (Li), cesium (Cs), barium (Ba), potassium (K), beryllium (Be), and calcium (Ca).

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~~34.~~ (Amended) A method according to claim ⁹~~7~~, wherein the insulating film comprises aluminum nitride.

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~~35.~~ (Amended) A method according to claim ~~3~~, wherein an organic resin is formed between the thin film transistor and the insulating film.

Please add new claims 36-40 as follows.

¹⁸ ~~36.~~ (New) A method according to claim ¹⁵~~7~~, wherein one of the pixel electrode and the second electrode comprises at least one selected from the group consisting of magnesium (Mg), lithium (Li), cesium (Cs), barium (Ba), potassium (K), beryllium (Be), and calcium (Ca).

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~~37.~~ (New) A method according to claim ²²~~4~~, wherein one of the pixel electrode and the second electrode comprises at least one selected from the group consisting of magnesium (Mg), lithium (Li), cesium (Cs), barium (Ba), potassium (K), beryllium (Be), and calcium (Ca).

²³
~~38.~~ (New) A method according to ~~claim 4~~, wherein the atmosphere is a dry nitrogen atmosphere.

³²
~~39.~~ (New) A method according to claim ²⁹~~5~~, wherein one of the pixel electrode and the second electrode comprises at least one selected from the group consisting of